

Low V_F Schottky Barrier Diode

Description

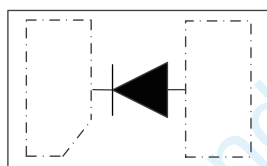
These Schottky barrier diodes are optimized for low forward voltage drop and low leakage current that offers the most optimal power dissipation in applications. They are housed in spacing saving micro-packaging ideal for space constraint applications.

Features

- ✧ Low Forward Voltage Drop: 300 mV (Max.) @ $I_F = 10$ mA
- ✧ Low Reverse Current: 10 μ A (Max.) @ $V_R = 20$ V
- ✧ 100 mA of Continuous Forward Current
- ✧ High Switching Speed
- ✧ Pb-Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- ✧ Low current rectification
- ✧ Camera Photo Flash
- ✧ Buck and Boost dc-dc Converters
- ✧ Reverse Voltage and Current Protection



Circuit Diagram



DFN0603

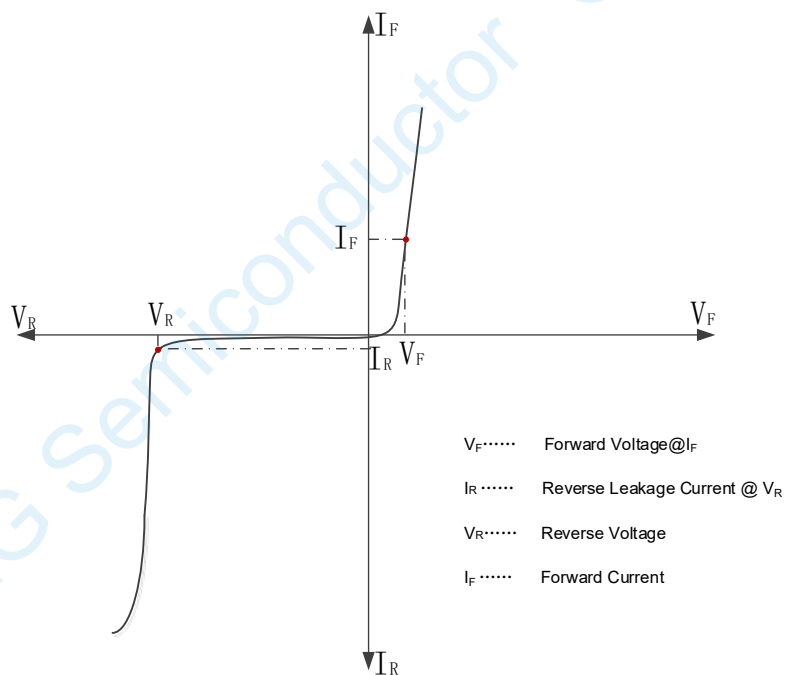
Absolute Maximum Rating ($T_A = 25$ °C, unless otherwise specified)

Rating	Symbol	Value	Units
Reverse Voltage (DC)	V_R	30	V
Forward Current (DC)	I_F	0.1	A
Forward Surge Current (60 Hz @ 1 cycle)	I_{FSM}	2	A
Junction temperature	T_j	125	°C
Storage temperature	T_{stg}	-40~+150	°C

Electrical Characteristics ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

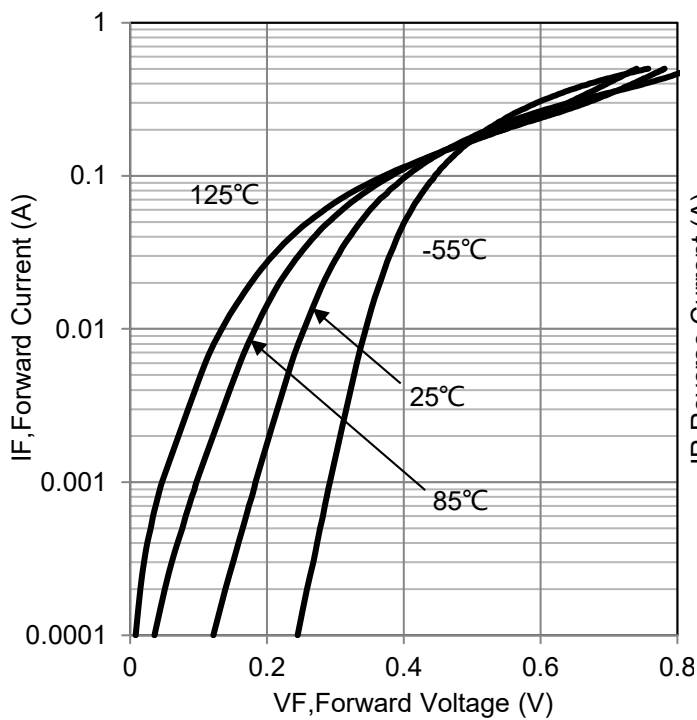
Parameter	Symbol	Conditions	Min.	Typical	Max.	Units
Reverse Leakage	I_R	$V_R=20\text{V}$			10	μA
Forward Voltage	V_F	$I_F=10\text{mA}$			0.30	V
Total Capacitance	C_T	$V_R = 0\text{V}$, $f = 1\text{MHz}$			10	pF

Electrical Parameters ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

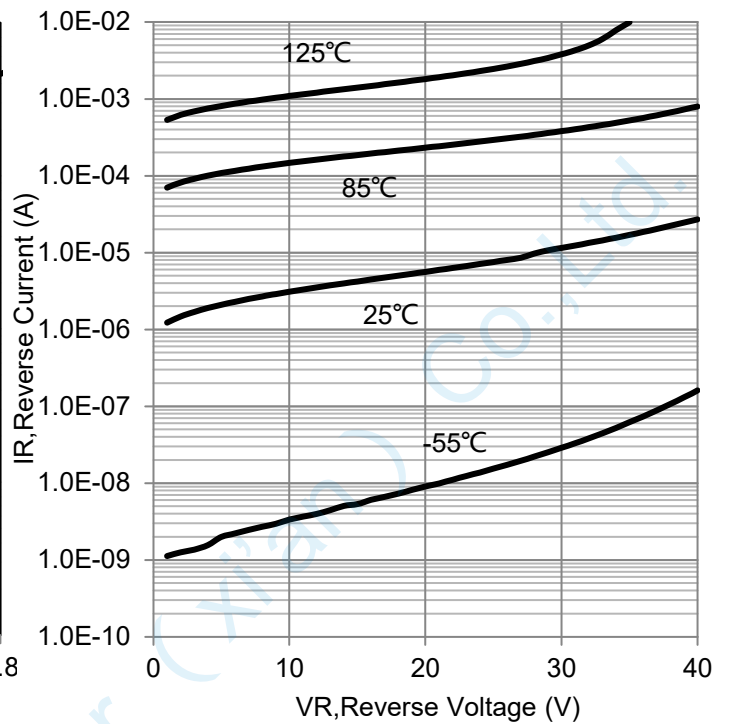


Typical Characteristics ($T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)

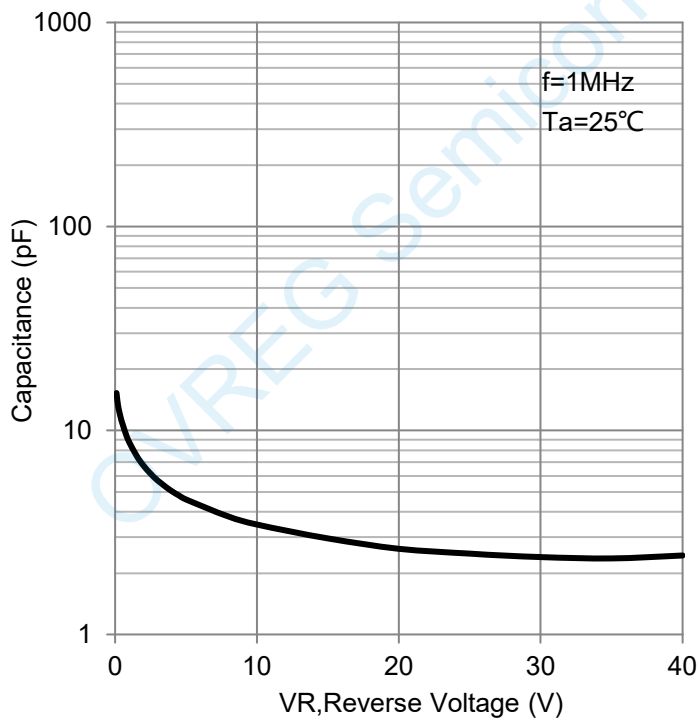
Forward Current vs. Forward Voltage



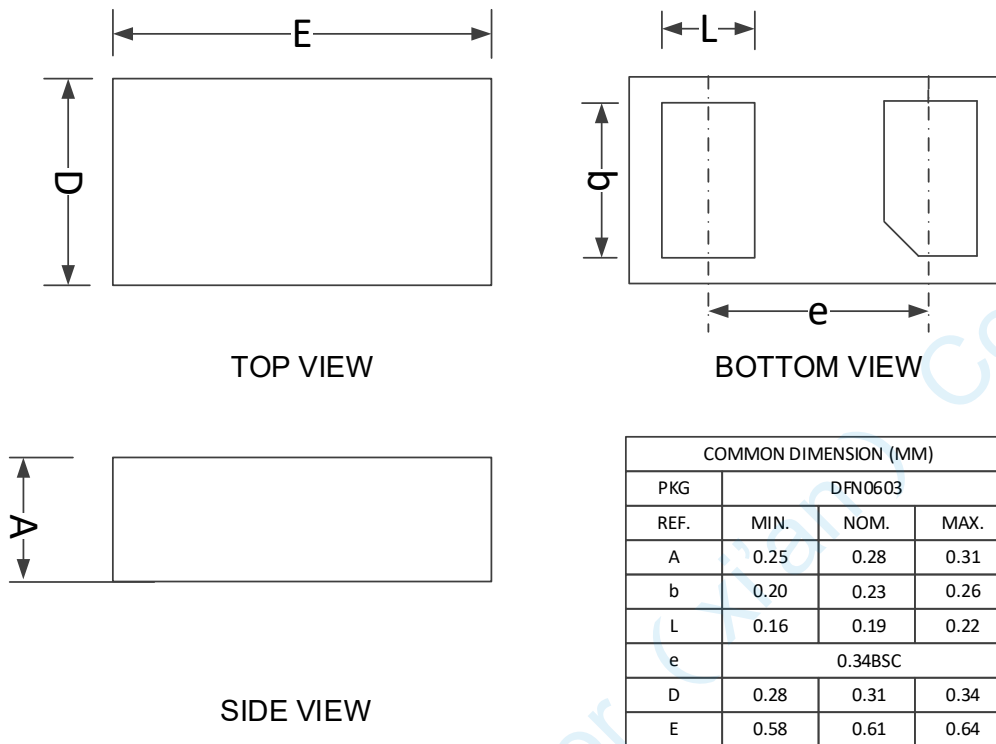
Reverse Characteristic



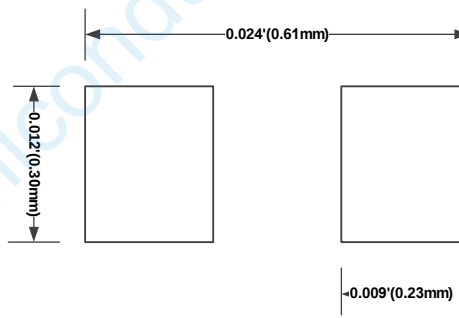
Capacitor Characteristics



Package Information



Recommend PCB Layout



Notes: This Pcb Layout Is For Reference Purposes Only

Marking



Ordering Information

Part number	Material	Type	Reel size	MOQ	MOQ/internal box	MOQ/carton
OVB02TL21A	GREEN	T/R	7 inch	12k/reel	10reel= 120k/box	4boxes=480k/carton